

GaAlAs/GaAs 1.8mm PACKAGE INFRARED EMITTING DIODE

MIE-184A4

Description

The MIE-184A4 is a high power infrared emitting diode in GaAs technology with AlGaAs window coating molded in water clear plastic package.

Features

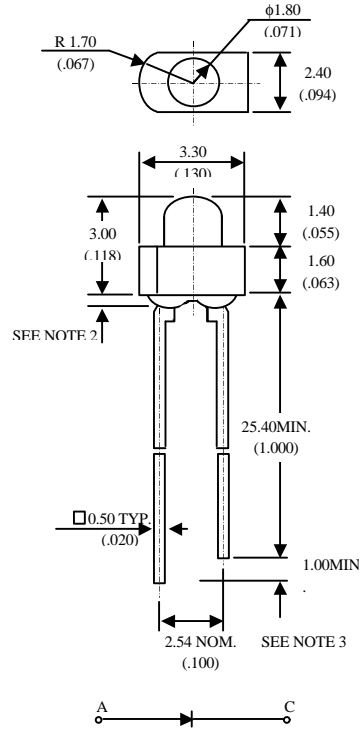
- High radiant power and high radiant intensity
- Suitable for DC and high pulse current operation
- Special 1.8mm package, radiation angle: 35°
- Peak wavelength $\lambda_p = 940$ nm
- Good spectral matching to Si-Photodetector

Application

- Data communication
- SIR

Package Dimensions

Unit : mm (inches)



Notes :

1. Tolerance is ± 0.25 mm (.010") unless otherwise noted.
2. Protruded resin under flange is 0.4 mm (.015") max.
3. Lead spacing is measured where the leads emerge from the package.

Absolute Maximum Ratings

@ $T_A = 25^\circ\text{C}$

Parameter	Maximum Rating	Unit
Power Dissipation	100	mW
Peak Forward Current(300pps,10 μ s pulse)	1	A
Continuous Forward Current	100	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C to +100°C	
Storage Temperature Range	-55°C to +100°C	
Lead Soldering Temperature	260°C for 5 seconds	

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Unity Opto Technology Co., Ltd.

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Optical-Electrical Characteristics

@ T_A=25°C

Parameter	Test Conditions	Symbol	Min.	Typ .	Max.	Unit
Radiant Intensity	I _F =20mA	I _e		2		mW/sr
Forward Voltage	I _F =50mA	V _F		1.3	1.5	V
Reverse Current	V _R =5V	I _R			10	μA
Peak Wavelength	I _F =20mA	λ		940		nm
Spectral Bandwidth	I _F =20mA	Δλ		50		nm
View Angle	I _F =20mA	2 θ _{1/2}		35		deg .

Typical Optical-Electrical Characteristic Curves

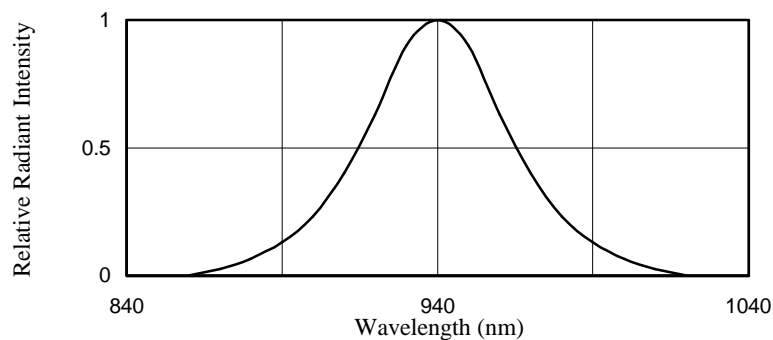


FIG.1 SPECTRAL DISTRIBUTION

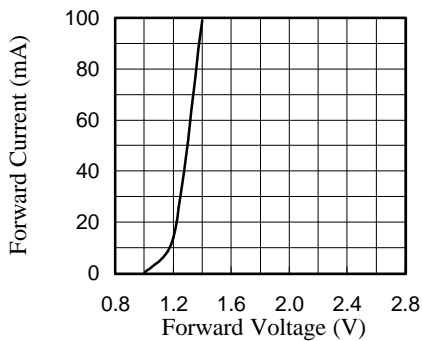


FIG.2 FORWARD CURRENT VS. FORWARD VOLTAGE

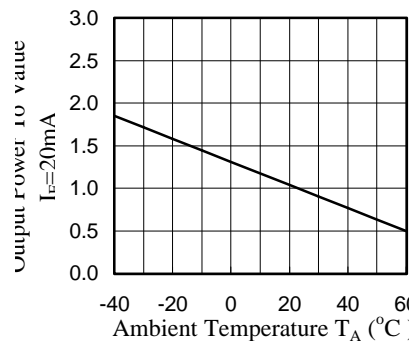


FIG.3 RELATIVE RADIANT INTENSITY VS. AMBIENT TEMPERATURE

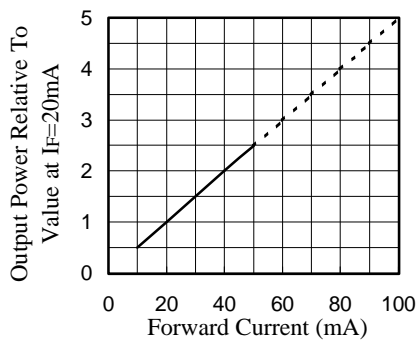


FIG.4 RELATIVE RADIANT INTENSITY VS. FORWARD CURRENT

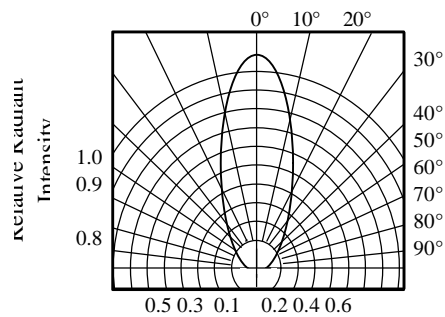


FIG.5 RADIATION DIAGRAM